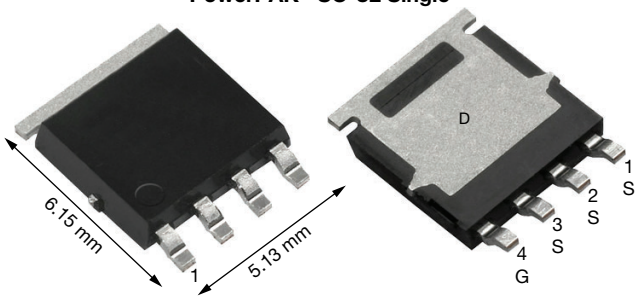
Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PowerPAK® SO-8L Single



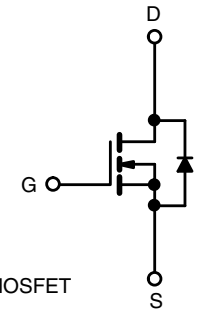
Top View Bottom View

FEATURES

- TrenchFET® power MOSFET
- 100 % R_g and UIS tested
- AEC-Q101 qualified
- Material categorization:
  for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE
Pb-free
RoHS COMPLIANT
HALOGEN FREE

PRODUCT SUMMARY	
V_{DS} (V)	40
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0034
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0043
I_D (A)	75
Configuration	Single
Package	PowerPAK SO-8L



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK® SO-8L
Lead (Pb)-free and halogen-free	SQJ422EP (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	40	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current	T_C = 25 °C	I_D	75	A
	T_C = 125 °C		62	
Continuous source current (diode conduction)		I_S	75	
Pulsed drain current [a]		I_{DM}	300	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	46	
Single pulse avalanche energy		E_{AS}	105	mJ
Maximum power dissipation	T_C = 25 °C	P_D	83	W
	T_C = 125 °C		27	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) [c]			260	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount [b]	R_{thJA}	65	°C/W
Junction-to-case (drain)		R_{thJC}	1.8	

Notes

a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
b. When mounted on 1" square PCB (FR4 material)
c. See solder profile (www.vishay.com/doc?73257). For PowerPAK SO-8L, the end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

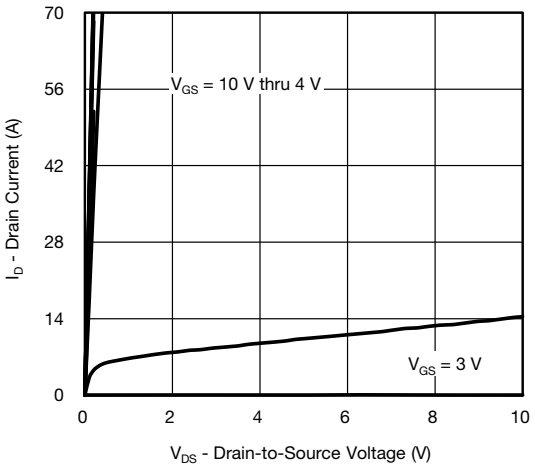
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0, I_D = 250 μA		40	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA		1.5	2.0	2.5	
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 40 V	-	-	1	μA
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 125 °C	-	-	50	
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 175 °C	-	-	150	
On-state drain current [a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	30	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 18 A	-	0.0028	0.0034	Ω
		V_{GS} = 4.5 V	I_D = 16 A	-	0.0035	0.0043	
		V_{GS} = 10 V	I_D = 18 A, T_J = 125 °C	-	-	0.0071	
		V_{GS} = 10 V	I_D = 18 A, T_J = 175 °C	-	-	0.0089	
Forward transconductance [b]	g_{fs}	V_{DS} = 15 V, I_D = 18 A		-	117	-	S
Dynamic [b]							
Input capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 20 V, f = 1 MHz	-	4616	5000	pF
Output capacitance	C_{oss}			-	420	691	
Reverse transfer capacitance	C_{rss}			-	182	278	
Total gate charge [c]	Q_g	V_{GS} = 10 V	V_{DS} = 20 V, I_D = 10 A	-	67	100	nC
Gate-source charge [c]	Q_{gs}			-	11.25	-	
Gate-drain charge [c]	Q_{gd}			-	10.31	-	
Gate resistance	R_g	f = 1 MHz		0.3	0.63	1.1	Ω
Turn-on delay time [c]	$t_{d(on)}$	V_{DD} = 20 V, R_L = 20 Ω I_D ≅ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		-	13	19	ns
Rise time [c]	t_r			-	10	15	
Turn-off delay time [c]	$t_{d(off)}$			-	29	44	
Fall time [c]	t_f			-	8	12	
Source-Drain Diode Ratings and Characteristics [b]							
Pulsed current [a]	I_{SM}			-	-	300	A
Forward voltage	V_{SD}	I_F = 12 A, V_{GS} = 0 V		-	0.75	1.1	V

Notes

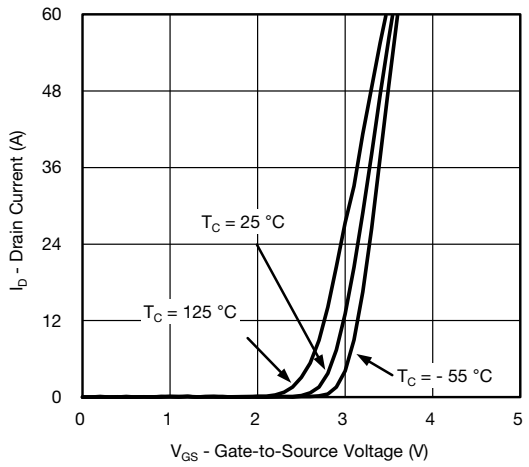
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

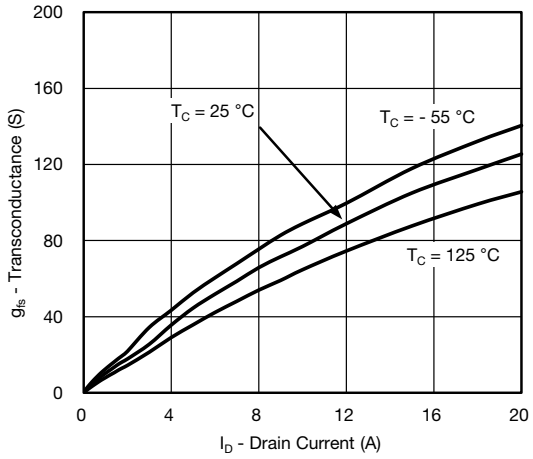
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



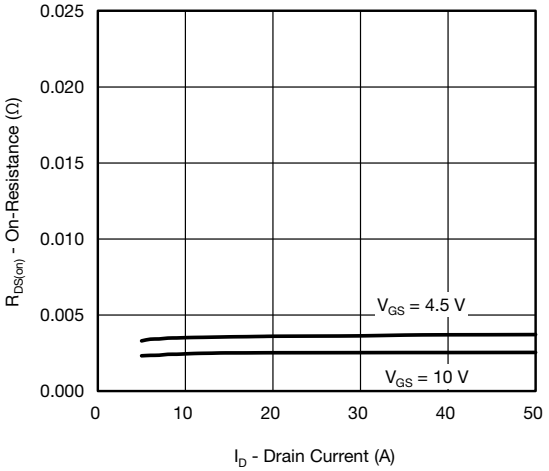
Output Characteristics



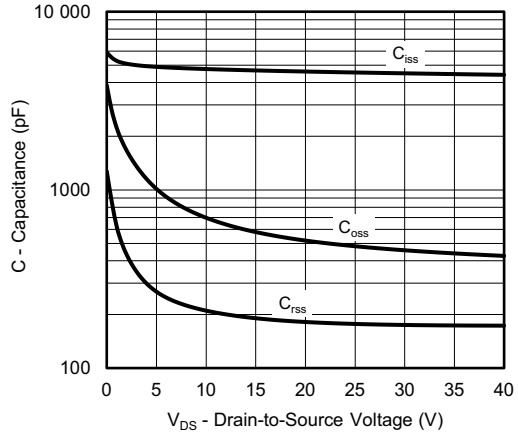
Transfer Characteristics



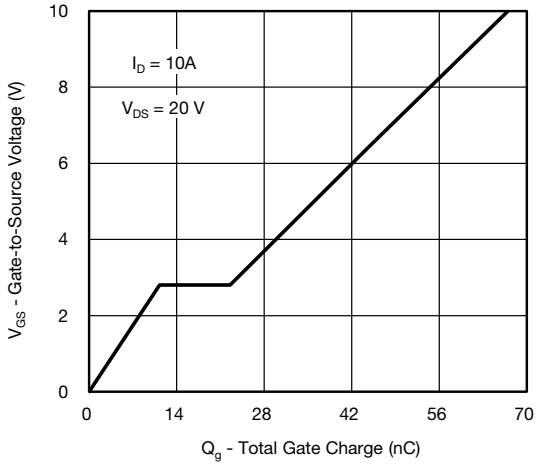
Transconductance



On-Resistance vs. Drain Current

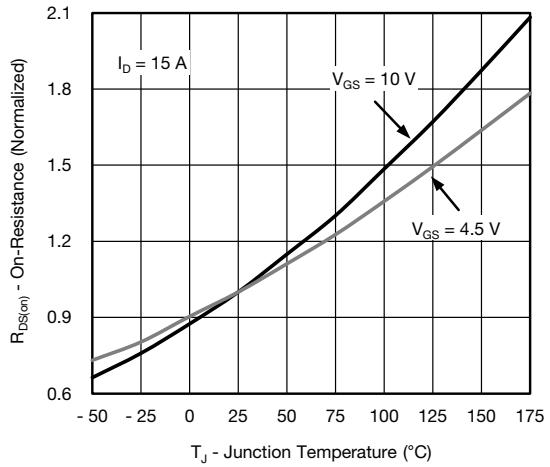


Capacitance

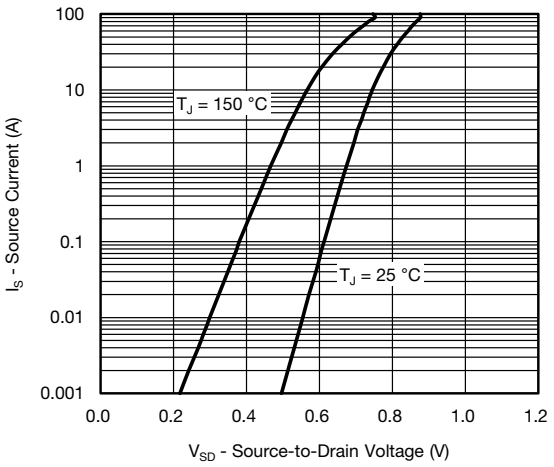


Gate Charge

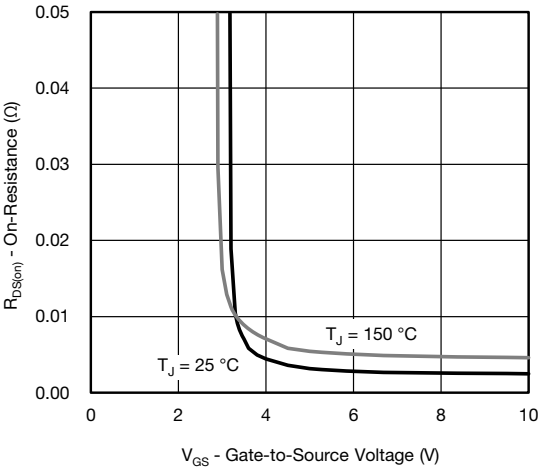
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



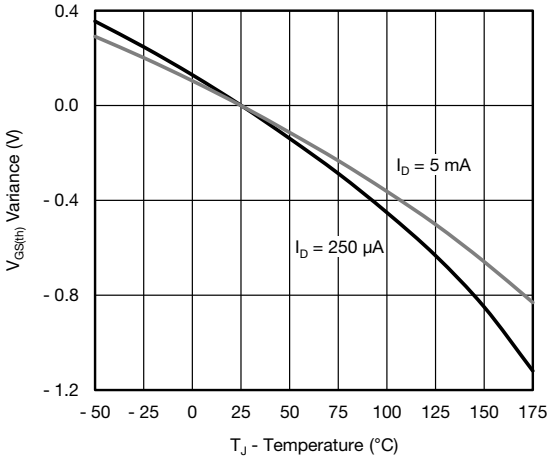
On-Resistance vs. Junction Temperature



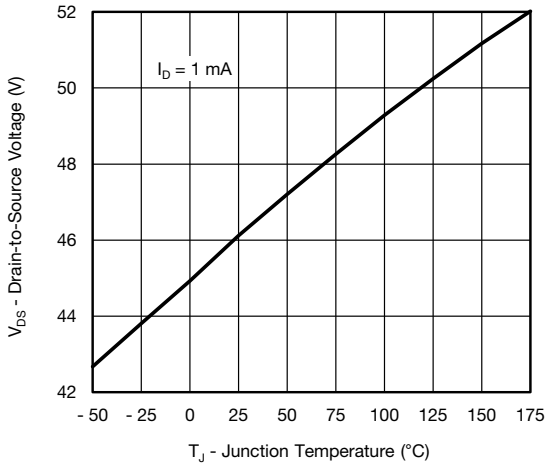
Source Drain Diode Forward Voltage



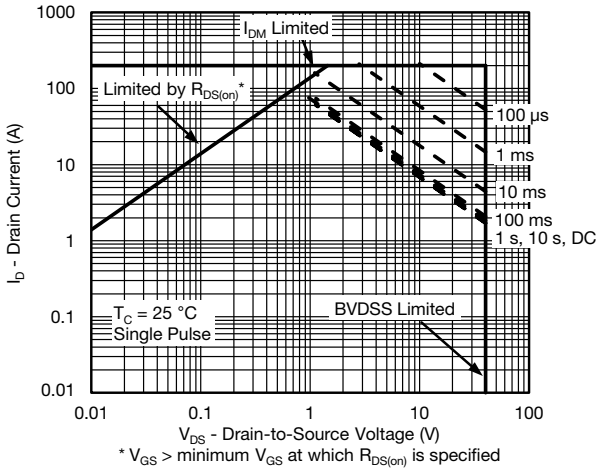
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

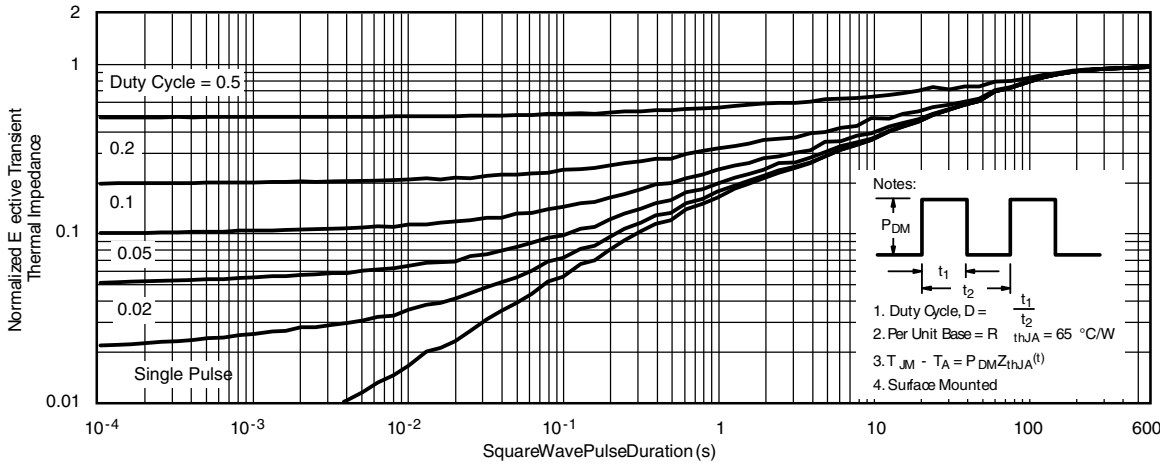


Drain Source Breakdown vs. Junction Temperature

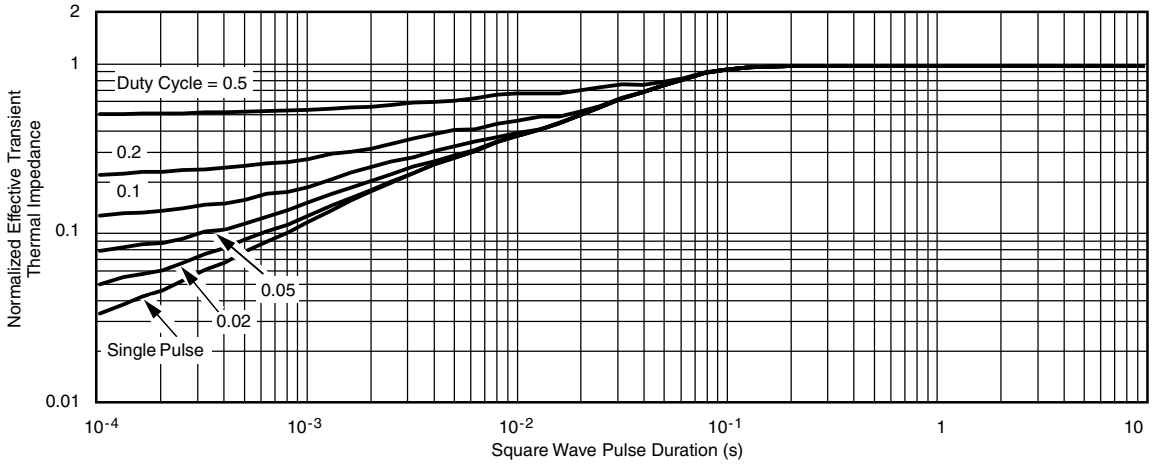


Safe Operating Area

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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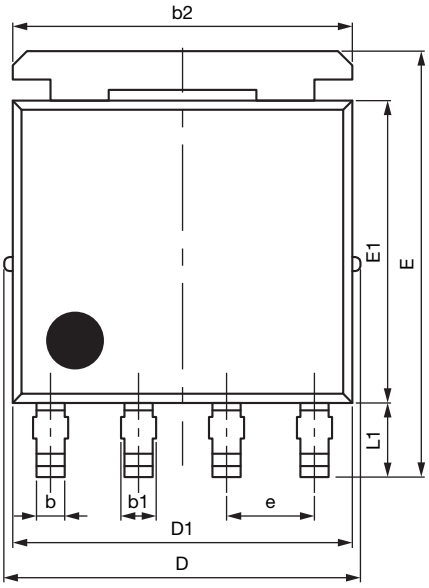
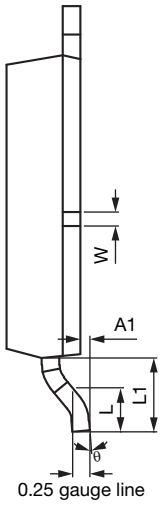
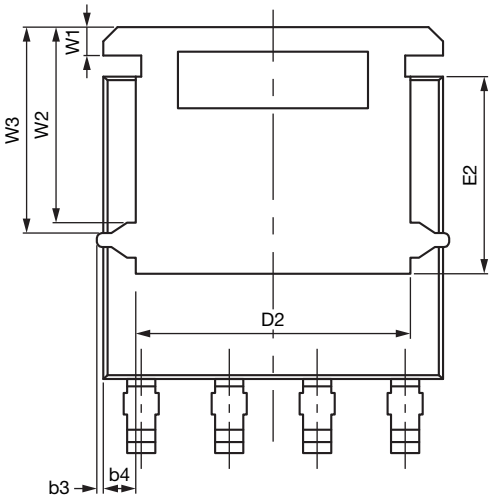
PowerPAK® SO-8L Case Outline 2

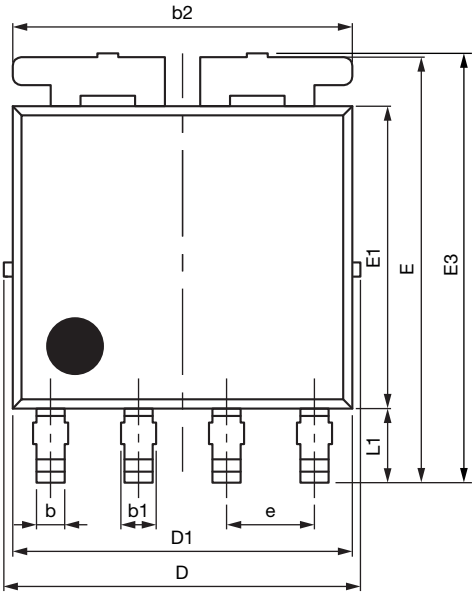


Topside view (single)

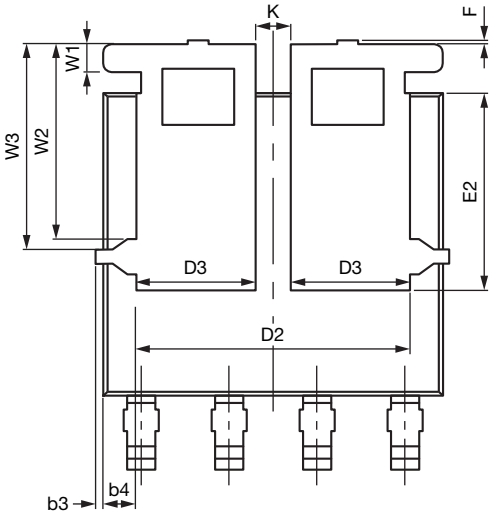




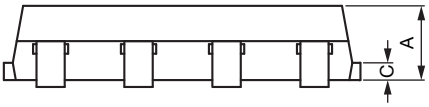
Backside view (single)



Topside view (dual)



Backside view (dual)

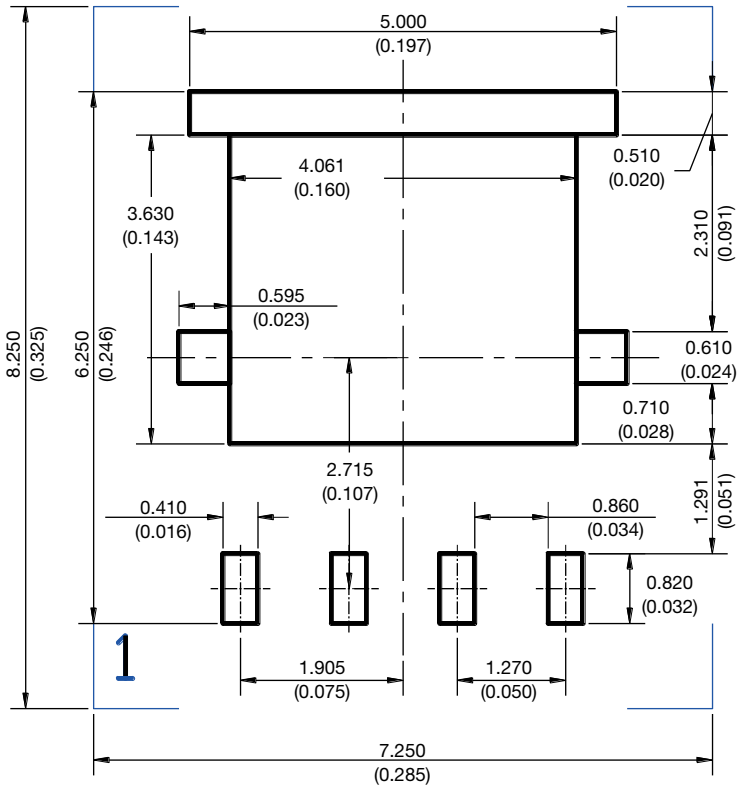


DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.094			0.004		
b4	0.47			0.019		
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	2.75	2.85	2.95	0.108	0.112	0.116
E3	6.05	6.22	6.40	0.238	0.245	0.252
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.51			0.020		
W	0.23			0.009		
W1	0.41			0.016		
W2	2.82			0.111		
W3	2.96			0.117		
θ	0°	-	10°	0°	-	10°
ECN: C23-1026-Rev. D, 25-Sep-2023 DWG: 6044						

Note

- Millimeters will govern

RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads
Dimensions in mm (inches)

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